L Number	Hits		DB	Time stamp
-	26032	(pr photoresist photo?resist polymer\$3) same	USPAT;	2004/04/17 18:23
		mask same (pattern aperture)	US-PGPUB	
-	2	((pr photoresist photo?resist polymer\$3)	USPAT;	2004/04/17 17:55
		same mask same (pattern aperture)) and	US-PGPUB	, ,
		(stretch\$3 with mask with align\$3 with	1	
		substrate)		
_	2	stretch\$3 with mask with align\$3 with	USPAT;	2004/04/17 17:56
		substrate	US-PGPUB	,,,,,,
_	20	l de la companya de	USPAT:	2004/07/15 11:22
		substrate	US-PGPUB	2001/07/13 11:22
i _	8	stretch\$3 same mask same align\$3 same	EPO; JPO;	2004/04/17 18:07
	Ū	substrate	DERWENT;	2004/04/17 18:07
		Bubbciace	IBM TDB	
_	3	reposition\$6 near35 polymer\$3 near5 mask	USPAT;	2004/07/14 37 44
-	3	repositions mealss polymerss meals mask	,	2004/07/14 17:44
	8095	(MDM and (mariat me mhatamaint))	US-PGPUB	2004/05/14 15 15
-	8095	(TFT and (resist pr photoresist))	USPAT;	2004/07/14 17:45
	6504	//	US-PGPUB	
-	6584	((TFT and (resist pr photoresist))) and mask	USPAT;	2004/07/14 17:45
	1010	///mm / /	US-PGPUB	: / /
-	1919	(((TFT and (resist pr photoresist))) and	USPAT;	2004/07/15 15:09
		mask) and aperture	US-PGPUB	
-	21	stretch\$3 same mask same align\$3 same	USPAT;	2004/07/15 11:25
		substrate	US-PGPUB	
-	10520	deposit\$3 near20 using near20 mask\$3	USPAT;	2004/07/15 13:14
			US-PGPUB	
-	1246	(deposit\$3 near20 using near20 mask\$3) and	USPAT;	2004/07/15 13:16
		(TFT (thin near3 film near3 transistor))	US-PGPUB	
-	196	deposit\$3 near50 using near50 polymer\$3	USPAT;	2004/07/15 13:15
		near50 mask\$3	US-PGPUB	
-	18	(deposit\$3 near50 using near50 polymer\$3	USPAT;	2004/07/15 13:53
		near50 mask\$3) and (TFT (thin near3 film	US-PGPUB	
		near3 transistor))	1	
-	2	flexable near3 polymer	USPAT;	2004/07/15 13:52
			US-PGPUB	
-	8501	((polymer organic) near50 mask)	USPAT;	2004/07/15 13:55
			US-PGPUB	
-	1073	(((polymer organic) near50 mask)) and (TFT	USPAT;	2004/07/15 13:55
		(thin near3 film near3 transistor))	US-PGPUB	
-	9406	((polymer\$3 organic) near50 mask)	USPAT;	2004/07/15 13:55
		_	US-PGPUB	
-	1115	(((polymer\$3 organic) near50 mask)) and (TFT	USPAT;	2004/07/15 13:56
		(thin near3 film near3 transistor))	US-PGPUB	
_	27	(((TFT and (resist pr photoresist))) and	EPO; JPO;	2004/07/15 15:34
		mask) and aperture	DERWENT;	, ,
		<u>-</u>	IBM TDB	
		L	I TOM IND	